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Title	Resonance assisted jump-in voltage reduction for electrostatically actuated nanobeam-based gateless NEM switches.
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Supplementary information

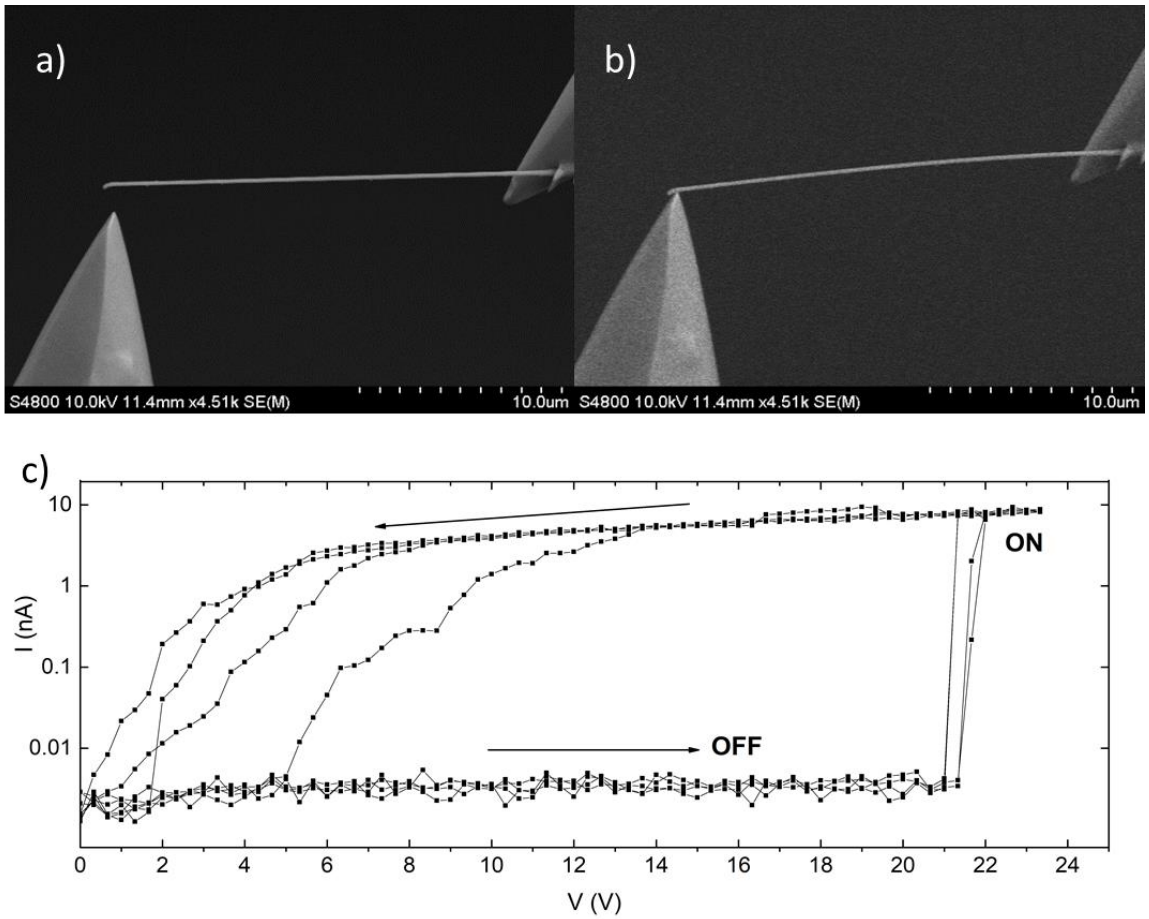

Figure 1. Additional NEM device with repeated measurements for GeSn nanowire with L = 22 µm, d = 125 nm. a) – nanowire in an OFF state; b) – nanowire in ON state, c) – repeated IV measurements of NEM device. The AC assisted jump in occurred at 5 V + 0.6 V DC + AC voltage.